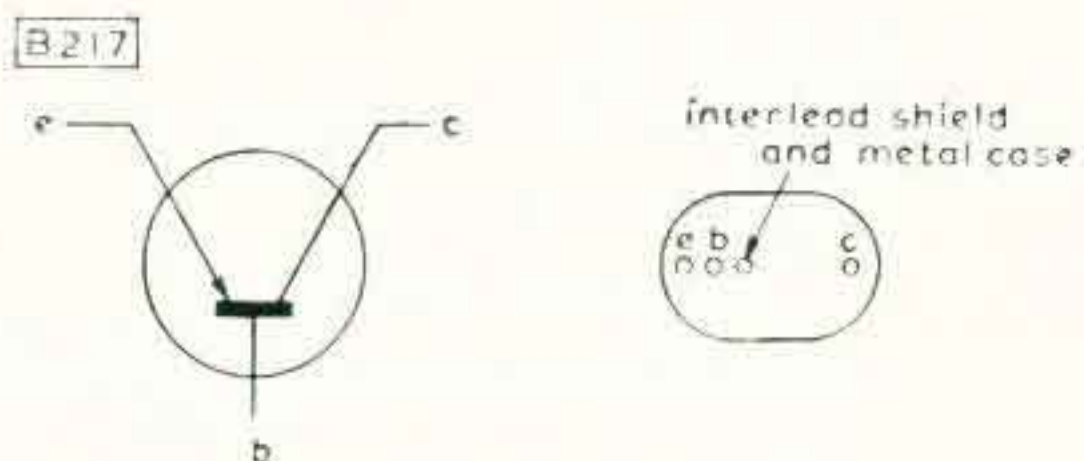


R.F. JUNCTION TRANSISTOR

OC170

R.F. junction transistor of the p-n-p alloy-diffused type intended for use as an r.f. amplifier or mixer oscillator in short-wave receivers or as an i.f. amplifier in a.m. and a.m./f.m. receivers.



DIMENSIONS

Max. body length	9.5	mm
Max. diameter	9.1	mm
Min. lead length	37	mm

ABSOLUTE MAXIMUM RATINGS

Collector voltage

$V_{cb(pk)}$ max.	-20	V
V_{cb} max.	-20	V
* $V_{ce(pk)}$ max.	-20	V
* V_{ce} max.	-20	V

*This value applies when $\frac{R_b}{R_e} < 100$ and $R_e > 200\Omega$

Collector current

$i_{c(pk)}$ max.	10	mA
I_c max.	10	mA

Emitter current

$i_{e(pk)}$ max.	10	mA
I_e max.	10	mA

Reverse emitter current

$i_{e(pk)}$ max.	1.0	mA
I_e max.	1.0	mA

Total dissipation

$$P_{tot} \text{ max.} = \frac{T_{\text{junction max.}} - T_{\text{ambient}}}{\theta}$$

Temperature ratings

Storage temperature limits	-55 to +75	°C
Maximum junction temperature		
Continuous operation	75	°C
‡Intermittent operation (total duration = 200 hours max.)	90	°C
Junction temperature rise above ambient, θ	0.6	°C/mW

‡Likelihood of full performance of a circuit at this temperature is also dependent on the type of application.



OC170 (Cont.)

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CHARACTERISTICS at $T_{\text{ambient}} = 25^{\circ}\text{C}$

		Typical Min.	production Typ.	spreads Max.	
Collector leakage current ($V_{cb} = -6\text{V}, I_e = 0\text{mA}$) ($V_{cb} = -20\text{V}, I_e = 0\text{mA}$)	I_{co}	—	1.5	13	μA
		—	—	50	μA
Emitter leakage current ($V_{eb} = -500\text{mV}, I_e = 0\text{mA}$)	I_{eo}	—	—	50	μA
Base current ($V_{cb} = -6\text{V}, I_e = 1\text{mA}$)	I_b	—	15	50	μA
Base input voltage ($V_{cb} = -6\text{V}, I_e = 1\text{mA}$)	V_{be}	-210	-260	-330	mV
Current amplification cut-off frequency at $V_{ce} = -6\text{V}, I_e = 1\text{mA}$ ($ \alpha' = 1$)	f_1	40	70	—	Mc/s
Current amplification factor ($V_{ce} = -6\text{V}, I_e = 1\text{mA}, f = 1\text{kc/s}$)	α'	20	100	—	
Noise figure ($V_{ce} = -6\text{V}, I_e = 1\text{mA}$) $R_{\text{source}} = 200\Omega, f = 500\text{kc/s}$ $R_{\text{source}} = 150\Omega, f = 10\text{Mc/s}$		—	3.0	8.0	dB
		—	4.0	8.0	dB
($V_{cb} = -6\text{V}, I_e = 1\text{mA}$) $R_{\text{source}} = 500\Omega, f = 1\text{kc/s}$		—	18	33	dB